



# BGU8051

## Low noise high linearity amplifier

Rev. 3 — 29 September 2014

Product data sheet

## 1. Product profile

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### 1.1 General description

The BGU8051 is a low noise high linearity amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 0.3 GHz and 1.5 GHz. It is housed in a 2 mm × 2 mm × 0.75 mm 8-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

### 1.2 Features and benefits

- Low noise performance:  $NF = 0.43$  dB
- High linearity performance:  $IP_{3O} = 39$  dBm
- High input return loss > 15 dB
- High output return loss > 20 dB
- Unconditionally stable
- Programmable bias current (via resistor)
- Small 8-terminal leadless package 2 mm × 2 mm × 0.75 mm
- ESD protection on all terminals
- Moisture sensitivity level 1
- Fast shutdown to support TDD systems
- +5 V single supply

### 1.3 Applications

- Wireless infrastructure
- Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- General purpose wireless applications
- TDD or FDD systems
- Suitable for small cells



1.4 Quick reference data

Table 1. Quick reference data

$f = 900\text{ MHz}$ ;  $V_{CC} = 5\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ ; input and output  $50\ \Omega$ ;  $R_{bias} = 5.1\text{ k}\Omega$ ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 15 with components listed in Table 9 optimized for  $f = 900\text{ MHz}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CC}$	supply current	on state	36	48	60	mA
		off state	-	2.8	-	mA
$G_{ass}$	associated gain	on state	17	18.3	20	dB
		off state	-	-21	-	dB
NF	noise figure		-	0.43	0.63	dB
$P_{L(1dB)}$	output power at 1 dB gain compression		-	19	-	dBm
$IP3O$	output third-order intercept point	2-tone; tone spacing = 1 MHz; $P_i = -15\text{ dBm}$ per tone	35	39	-	dBm

2. Pinning information

2.1 Pinning

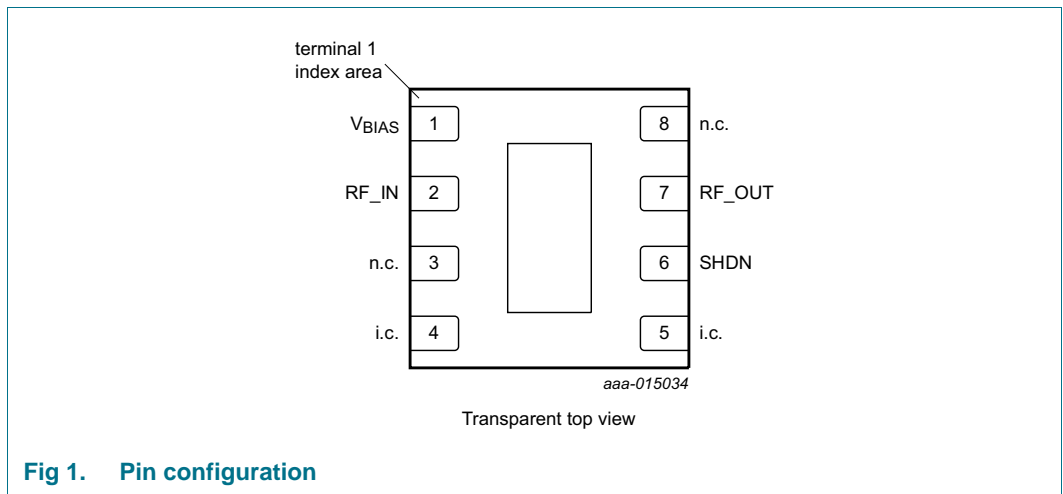


Fig 1. Pin configuration

2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$V_{BIAS}$	1	bias voltage
RF_IN	2	RF input
n.c.	3, 8	not connected
i.c.	4, 5	internally connected. Can be grounded or left open in the application
SHDN	6	shutdown
RF_OUT	7	RF output
GND	exposed die pad	ground

### 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BGU8051	HWSO8	plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body 2 × 2 × 0.75 mm	SOT1327-1

### 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-	6	V
V <sub>ctrl(sd)</sub>	shutdown control voltage		-	3	V
I <sub>CC</sub>	supply current		-	85	mA
P <sub>I(RF)CW</sub>	continuous waveform RF input power		-	20	dBm
T <sub>stg</sub>	storage temperature		-40	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
P	power dissipation	T <sub>case</sub> ≤ 125 °C [1]	-	510	mW
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001-2010	-	0.9	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B	-	2	kV

[1] Case is ground solder pad.

### 5. Recommended operating conditions

**Table 5. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage		4.75	5	5.25	V
Z <sub>0</sub>	characteristic impedance		-	50	-	Ω
T <sub>case</sub>	case temperature		-40	-	+85	°C

### 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
R <sub>th(j-case)</sub>	thermal resistance from junction to case		[1][2] 50	K/W

[1] Case is ground solder pad.

[2] Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

## 7. Characteristics

**Table 7. Characteristics**

$f = 900$  MHz;  $V_{CC} = 5$  V;  $T_{amb} = 25$  °C; input and output  $50 \Omega$ ;  $R_{bias} = 5.1$  k $\Omega$ ; unless otherwise specified. All RF parameters are measured in an application board as shown in [Figure 15](#) with components listed in [Table 9](#) optimized for  $f = 900$  MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CC</sub>	supply current	on state	36	48	60	mA
		off state	-	2.8	-	mA
G <sub>ass</sub>	associated gain	on state	17	18.3	20	dB
		off state	-	-21	-	dB
NF	noise figure		-	0.43	0.63	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	19	-	dBm
IP <sub>3O</sub>	output third-order intercept point	2-tone; tone spacing = 1 MHz; P <sub>i</sub> = -15 dBm per tone	35	39	-	dBm
		2-tone; tone spacing = 1 MHz; P <sub>i</sub> = -15 dBm per tone <sup>[1]</sup>	33	37	-	dBm
RL <sub>in</sub>	input return loss	on state	-	15.9	-	dB
		off state	-	12.5	-	dB
RL <sub>out</sub>	output return loss		-	29	-	dB
ISL	isolation		-	21	-	dB
t <sub>s(pon)</sub>	power-on settling time	P <sub>i</sub> = -20 dBm; SHDN (pin 6) from HIGH to LOW <sup>[1]</sup>	-	1.4	-	μs
t <sub>s(poff)</sub>	power-off settling time	P <sub>i</sub> = -20 dBm; SHDN (pin 6) from LOW to HIGH <sup>[1]</sup>	-	0.4	-	μs
K	Rollett stability factor	both on state and off state up to $f = 20$ GHz	1	-	-	
R <sub>pd(SHDN)</sub>	pull-down resistance on pin SHDN		-	10	-	k $\Omega$

[1] For applications where fast switching is required, it is recommended to change C1 and C2 to 100 pF.

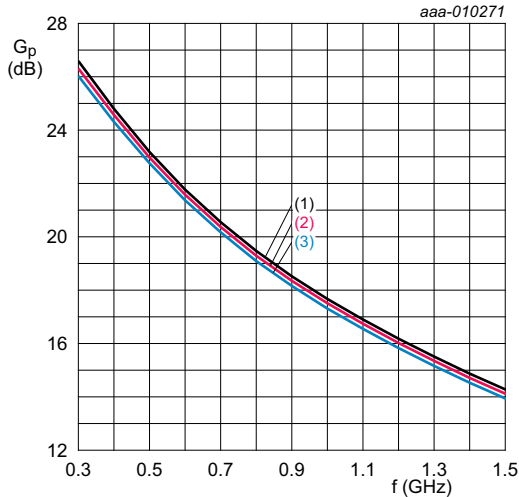
**Table 8. Shutdown control**

$V_{CC} = 5$  V;  $T_{amb} = 25$  °C; input and output  $50 \Omega$ ;  $R_{bias} = 5.1$  k $\Omega$ ; unless otherwise specified. All RF parameters are measured in an application board as shown in [Figure 15](#) with components listed in [Table 9](#) optimized for  $f = 900$  MHz.

State	V <sub>ctrl(sd)</sub> <sup>[1]</sup> (V)
on state	≤ 0.6
off state	≥ 1.2

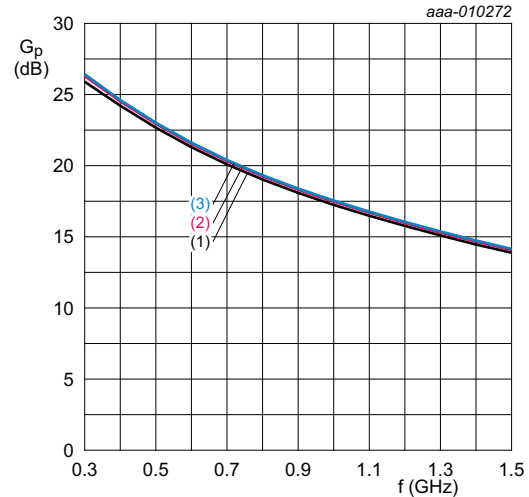
[1] Voltage on pin 6 (SHDN).

7.1 Graphs



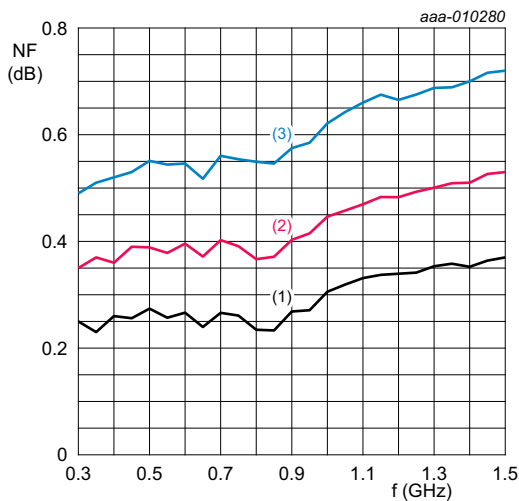
$V_{CC} = 5\text{ V}; I_{CC} = 48\text{ mA}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +85\text{ }^{\circ}\text{C}$

**Fig 2. Power gain as a function of frequency; typical values**



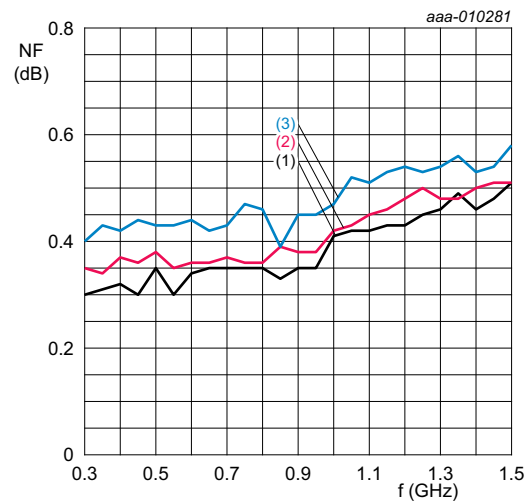
$V_{CC} = 5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $I_{CC} = 30\text{ mA}$   
 (2)  $I_{CC} = 45\text{ mA}$   
 (3)  $I_{CC} = 60\text{ mA}$

**Fig 3. Power gain as a function of frequency; typical values**



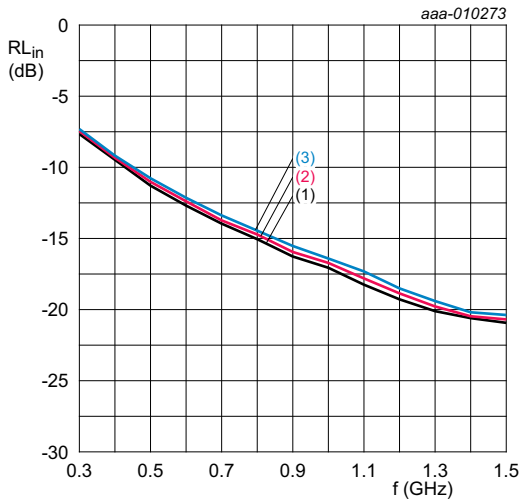
$V_{CC} = 5\text{ V}; I_{CC} = 48\text{ mA}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +85\text{ }^{\circ}\text{C}$

**Fig 4. Noise figure as a function of frequency; typical values**



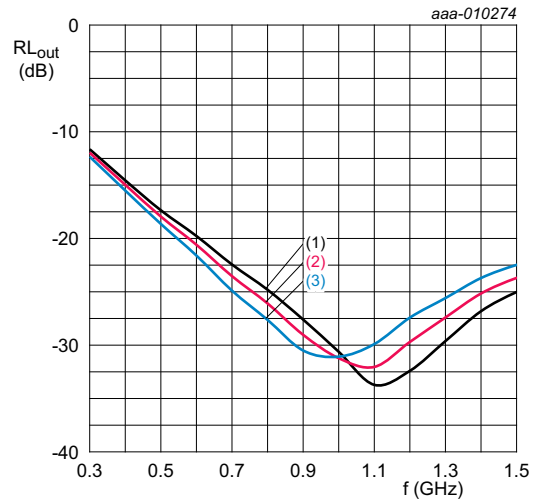
$V_{CC} = 5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}.$   
 (1)  $I_{CC} = 30\text{ mA}$   
 (2)  $I_{CC} = 45\text{ mA}$   
 (3)  $I_{CC} = 60\text{ mA}$

**Fig 5. Noise figure as a function of frequency; typical values**



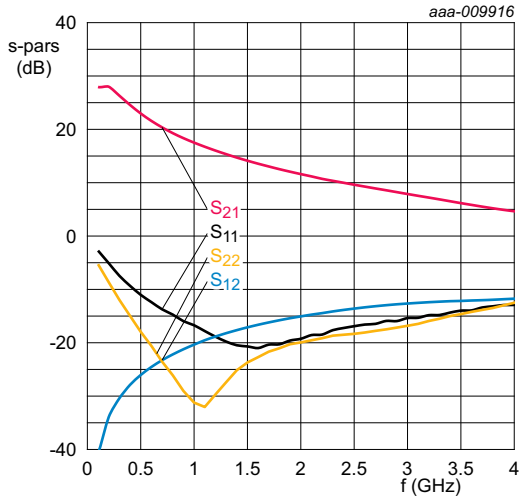
$V_{CC} = 5\text{ V}; I_{CC} = 48\text{ mA}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +85\text{ }^{\circ}\text{C}$

**Fig 6. Input return loss as a function of frequency; typical values**



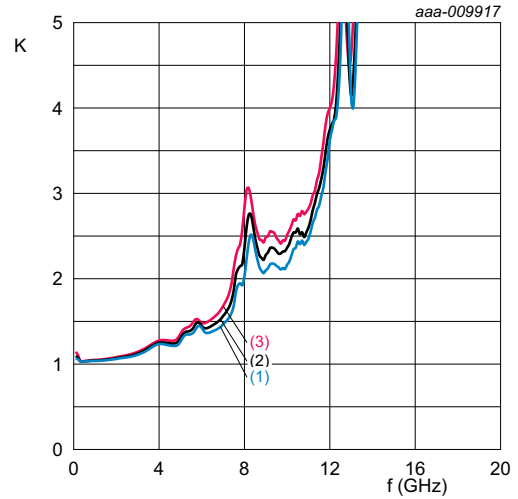
$V_{CC} = 5\text{ V}; I_{CC} = 48\text{ mA}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +85\text{ }^{\circ}\text{C}$

**Fig 7. Output return loss as a function of frequency; typical values**



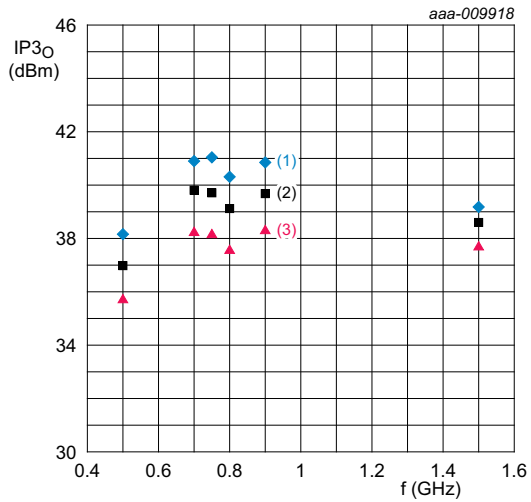
$V_{CC} = 5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; I_{CC} = 48\text{ mA}.$

**Fig 8. Wideband S-parameters as function of frequency; typical values**



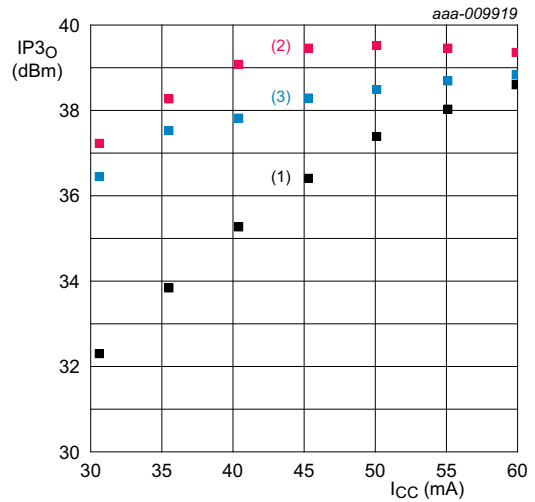
$V_{CC} = 5\text{ V}; I_{CC} = 48\text{ mA}.$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = +25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = +85\text{ }^{\circ}\text{C}$

**Fig 9. Rollet stability factor as a function of frequency; typical values**



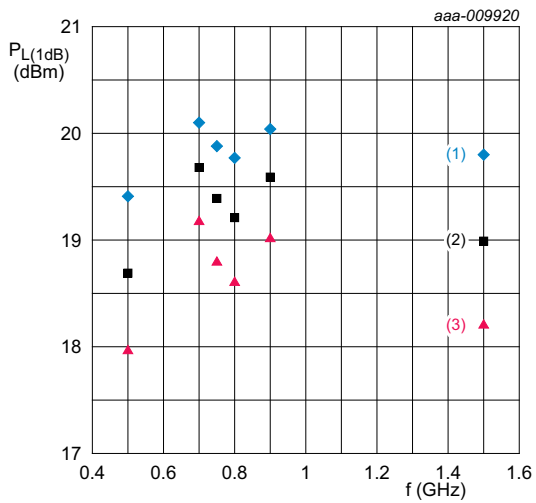
$V_{CC} = 5\text{ V}$ ;  $P_i = -15\text{ dBm}$  per tone;  $I_{CC} = 48\text{ mA}$ .  
 (1)  $T_{amb} = -40\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = +25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = +85\text{ }^\circ\text{C}$

**Fig 10. Output third-order intercept point as a function of frequency; typical values**



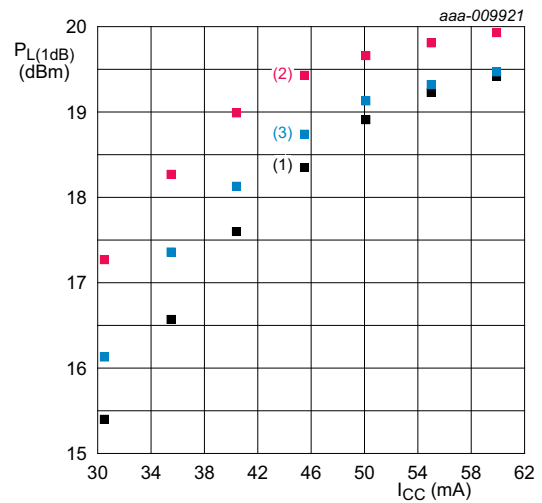
$V_{CC} = 5\text{ V}$ ;  $P_i = -15\text{ dBm}$  per tone;  $T_{amb} = 25\text{ }^\circ\text{C}$ .  
 (1)  $f = 500\text{ MHz}$   
 (2)  $f = 900\text{ MHz}$   
 (3)  $f = 1500\text{ MHz}$

**Fig 11. Output third-order intercept point as a function of supply current; typical values**



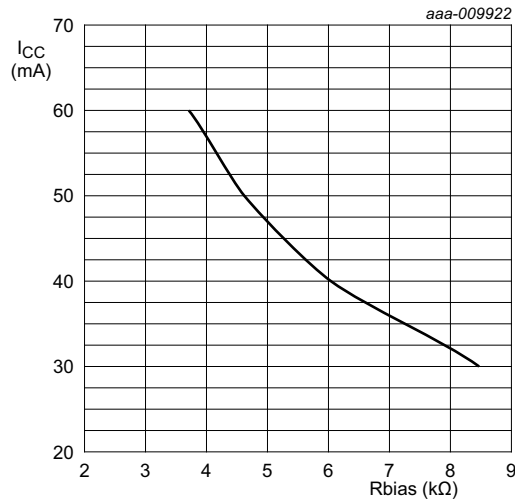
$V_{CC} = 5\text{ V}$ ;  $I_{CC} = 48\text{ mA}$ .  
 (1)  $T_{amb} = -40\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = +25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = +85\text{ }^\circ\text{C}$

**Fig 12. Output power at 1 dB gain compression as a function of frequency; typical values**



$V_{CC} = 5\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ .  
 (1)  $f = 500\text{ MHz}$   
 (2)  $f = 900\text{ MHz}$   
 (3)  $f = 1500\text{ MHz}$

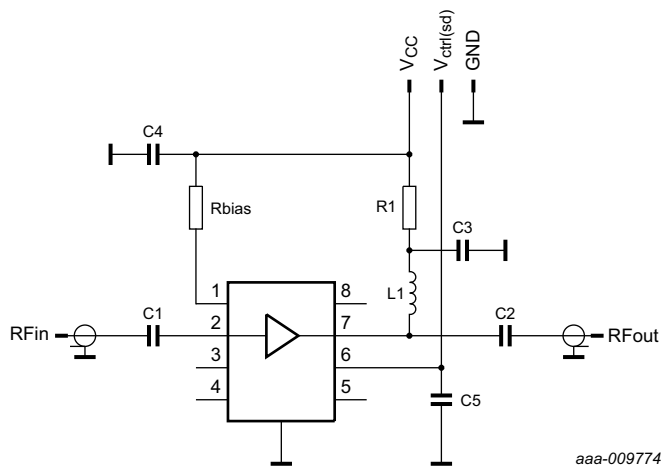
**Fig 13. Output power at 1 dB gain compression as a function of supply current; typical values**



V<sub>CC</sub> = 5 V.

Fig 14. Supply current as a function of Rbias; typical values

## 8. Application information



See [Table 9](#) for a list of components.

Fig 15. Schematic of application board

Table 9. List of components

See [Figure 15](#) for schematics.

Component	Description	Value	Remarks
C1, C2	capacitor	100 nF	
		100 pF	recommended for TDD systems
C3, C5	capacitor	10 pF	
C4	capacitor	10 nF	



**Table 9. List of components ...continued**  
See [Figure 15](#) for schematics.

Component	Description	Value	Remarks
L1	inductor	33 nH	
R1	resistor	10 Ω	
Rbias	resistor	5.1 kΩ	

**Table 10. Typical performance BGU8051 application board**

All RF parameters are measured at the application board as shown in [Figure 15](#) with the components as listed in [Table 9](#) while optimized for:  $f = 900$  MHz;  $V_{CC} = 5$  V;  $I_{CC} = 48$  mA and  $T_{amb} = 25$  °C, unless otherwise specified.

Symbol	Parameter	Conditions	f (MHz)						
			400	500	700	750	800	900	1500
$G_{ass}$	associated gain		24.6	23.0	20.4	19.8	19.3	18.3	14.1
$RL_{in}$	input return loss		9.3	11.0	13.7	14.2	14.7	15.9	20.7
$RL_{out}$	output return loss		15.0	18.0	23.5	24.8	26.1	29.0	23.7
$P_{L(1dB)}$	output power at 1 dB gain compression		18.0	18.7	19.7	19.4	19.2	19.6	19.0
$IP3O$	output third-order intercept point	$P_i = -15$ dBm per tone <a href="#">[1]</a>							
		$C1 = C2 = 100$ nF <a href="#">[1]</a>	-	-	-	39.7	39.1	39.7	38.6
		$C1 = C2 = 100$ pF <a href="#">[1][2]</a>	-	-	-	37.9	35.1	37.8	36.6
		$P_i = -25$ dBm per tone <a href="#">[1]</a>							
		$C1 = C2 = 100$ nF <a href="#">[1]</a>	36.7	38.5	39.8	-	-	-	-
		$C1 = C2 = 100$ pF <a href="#">[1][2]</a>	35.6	36.4	37.0	-	-	-	-
NF	noise figure	<a href="#">[3]</a>	0.41	0.39	0.40	0.39	0.37	0.40	0.53

[1] 2-Tone; tone spacing = 1 MHz.

[2] For TDD systems C1 and C2 have to be 100 pF.

[3] Connector and board losses not de-embedded.



## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile Communication
HBM	Human Body Model
LNA	Low Noise Amplifier
LTE	Long Term Evolution
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8051 v.3	20140929	Product data sheet	-	BGU8051 v.2
Modifications:	<ul style="list-style-type: none"> <li><a href="#">Figure 1 on page 2</a>: figure has been corrected</li> </ul>			
BGU8051 v.2	20131230	Product data sheet	-	BGU8051 v.1
BGU8051 v.1	20131127	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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